Contribution ID: **21** Type: **not specified**

Electric Field Modeling by simulations with ISE-TCAD

Thursday 31 May 2012 14:00 (20 minutes)

Simulations of a pad silicon sensor (100 x 300 μm) have been carried out in order to model the electric field distribution under irradiation as proposed by V.Eremin. The electric field distribution has been compared at different bias voltages and for several irradiation doses with the two midgap level model.
The software package used has been ISE-TCAD which allows to simulate the electrical parameters of the device.

Author: MINANO MOYA, Mercedes (Universidad de Valencia (ES))

Presenter: MINANO MOYA, Mercedes (Universidad de Valencia (ES))

Session Classification: Detector Characterization and Simulations

Track Classification: Detector Characterization